

LNC701PS

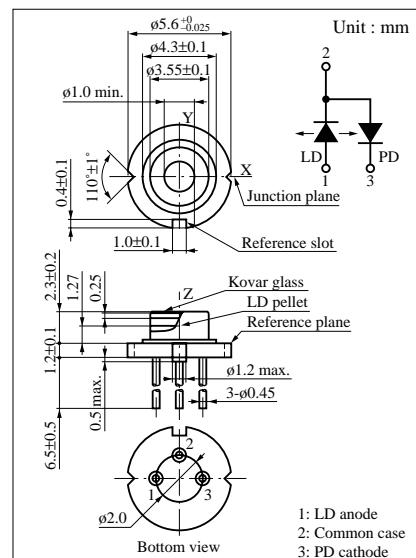
GaAlAs Semiconductor Laser

■ Features

- Low threshold current
- Stable single horizontal mode oscillation
- Long lifetime, high reliability

■ Applications

- Optical data processing devices
- Optical disk memory drive
- Optical measuring equipment



■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Radiant power	P_O	35	mW
Reverse voltage	Laser V_R	2	V
	PIN V_R (PIN)	30	V
Power dissipation	P_d (PIN)	100	mW
Operating ambient temperature	T_{opr}	-10 to +60	°C
Storage temperature	T_{stg}	-40 to +80	°C

■ Electro-Optical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Threshold current	I_{th}	CW	10	20	30	mA
Operating current	I_{OP}	CW $P_O = 30\text{mW}$	30	55	70	mA
Operating voltage	V_{OP}	CW $P_O = 30\text{mW}$		2.0	2.5	V
Oscillation wavelength	λ_L	CW $P_O = 30\text{mW}$	780	785	790	nm
Radiation angle	$\theta_{//}$	CW $P_O = 30\text{mW}$	8.5	10	11.5	deg.
	θ_{\perp}	CW $P_O = 30\text{mW}$	23	25	28	deg.
Differential efficiency	η	CW $P_O = 3 - 30\text{mW}$	0.8	1.0	1.2	
PIN photo current	I_P	CW $P_O = 30\text{mW}, V_R(\text{PIN}) = 5\text{V}$		0.3		mA
Reverse current (DC)	I_R	$V_R(\text{PIN}) = 15\text{V}$			0.1	μA
Optical axis accuracy	X direction θ_X	CW $P_O = 30\text{mW}$	-2.0		+2.0	deg.
	Y direction θ_Y	CW $P_O = 30\text{mW}$	-3.0		+3.0	deg.

*1 The radiation angle is indicated as the full angle at half maximum.

